



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

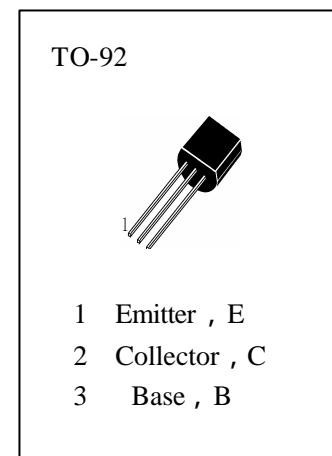
H562

APPLICATIONS

Low frequency power amplifier.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg}	—Storage Temperature.....	-55~150
T_j	—Junction Temperature.....	150
P_c	—Collector Dissipation.....	500mW
V_{CBO}	—Collector-Base Voltage.....	-35V
V_{CEO}	—Collector-Emitter Voltage.....	-30V
V_{EBO}	—Emitter-Base Voltage.....	-5V
I_c	—Collector Current.....	-500mA
I_e	—Emitter Current.....	500mA



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector Cut-off Current			-100	nA	$V_{CB}=-35V, I_E=0$
I_{EBO}	Emitter Cut-off Current			-100	nA	$V_{EB}=-5V, I_C=0$
$H_{FE} (1)$	DC Current Gain	70		240		$V_{CE}=-1V, I_C=-100mA$
$H_{FE} (2)$	DC Current Gain	25				$V_{CE}=-6V, I_C=-400mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		-0.1	-0.25	V	$I_C=-100mA, I_B=-10mA$
V_{BE}	Base-Emitter Voltage		-0.8	-1.0	V	$V_{CE}=1V, I_C=100mA$
f_T	Current Gain- Bandwidth Product	150	200		MHz	$V_{CE}=-6V, I_C=-20mA$
C_{ob}	Output Capacitance		13		pF	$V_{CB}=-6V, I_E=0, f=1MHz$

h_{FE} Classification

O

70—140

Y

120—240